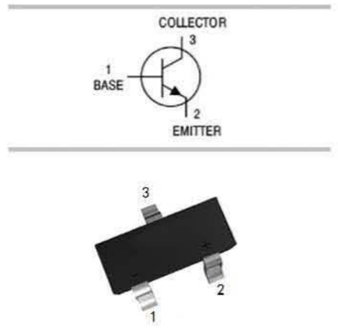
KTC3880

FEATURES

- High current gain bandwidth product.
- power dissipation.(P_C=200mW)

APPLICATIONS

- NPN epitaxial silicon transistor.



SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	200	mA
P_C	Collector Dissipation	200	mW
$T_{j,}T_{stg}$	Junction and Storage Temperature	-55~150	℃

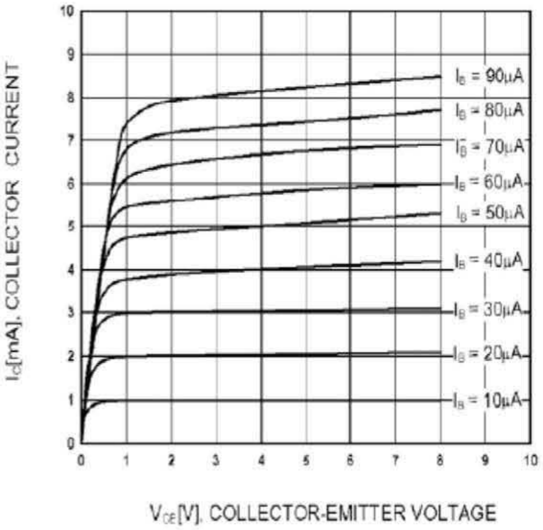
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

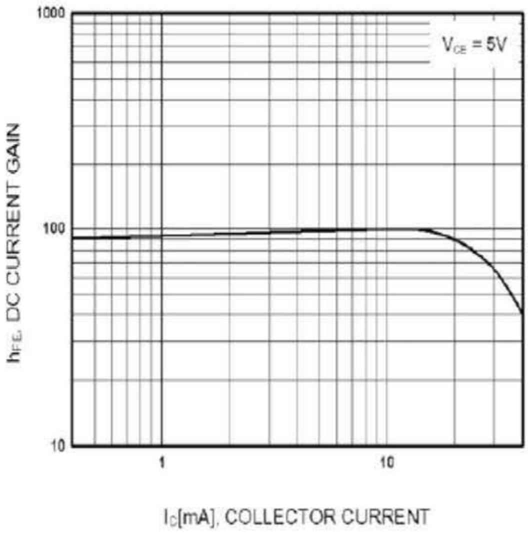
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=0.1mA,I_B=0	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=15V,I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=5V,I_C =1mA	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10 mA, I_B= 1mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=10 mA, I_B= 1mA			1.4	V
Transition frequency	f_T	V_{CE}=5V, I_C= 5mA f=400MHz	600			MHz

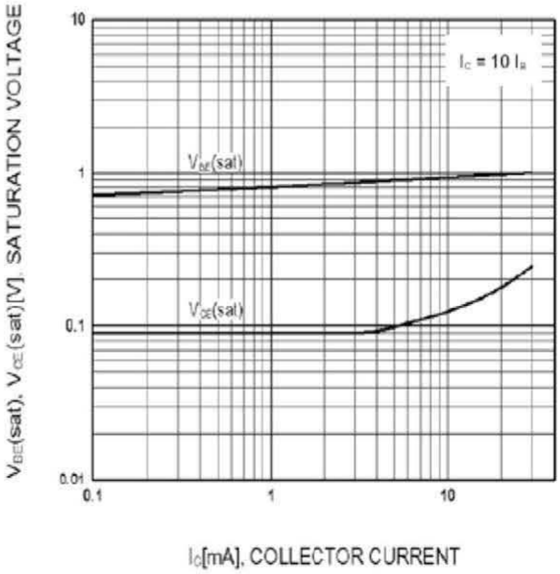
h_{FE}

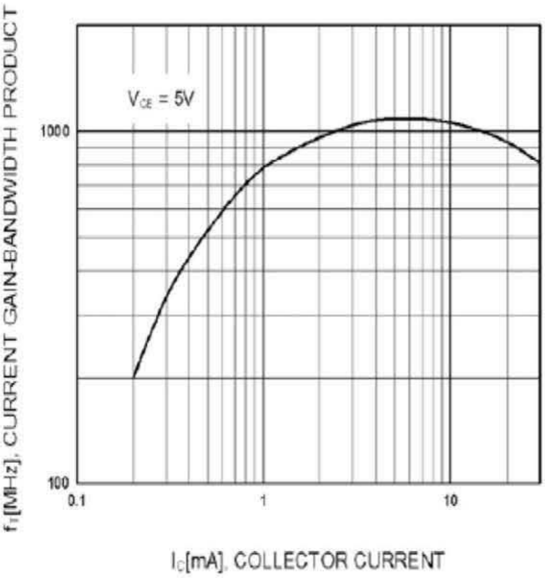
*	R	O	Y
hFE	40~80	70~140	100~200

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified



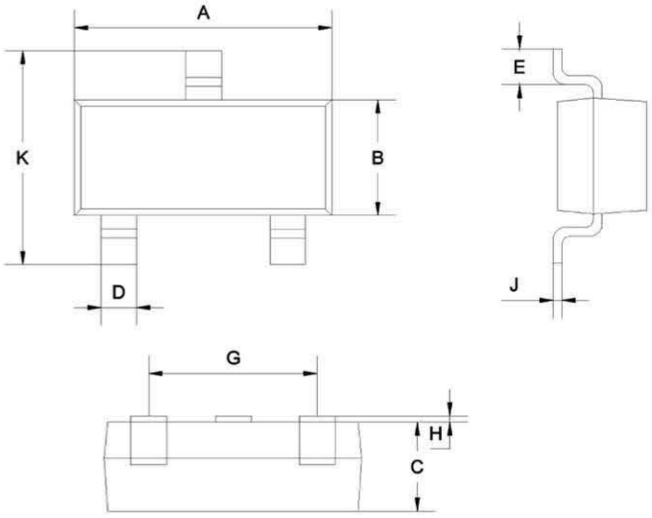






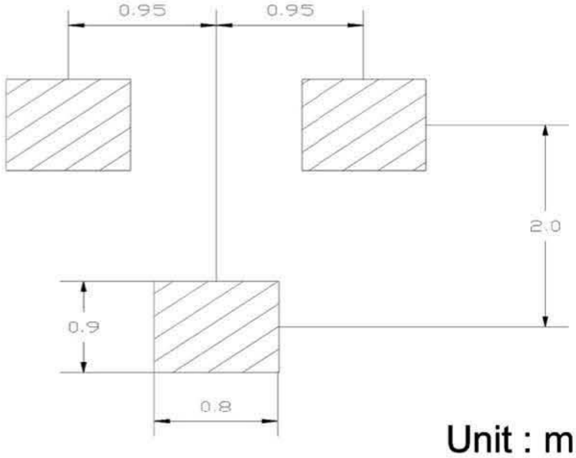
PACKAGE OUTLINE

Plastic surface mounted package



SOT-23		
Dim	Min	Max
A	2.85	2.95
B	1.25	1.35
C	1.0Typical	
D	0.37	0.43
E	0.35	0.48
G	1.85	1.95
H	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm